

CD2535H1

主要参数 MAIN CHARACTERISTICS

$I_{T(AV)}$	25A
V_{DRM}/V_{RRM}	1000V
I_{GT}	10-35mA

用途

半交流开关
 相位控制

APPLICATIONS

Half AC switching
 Phase control

产品特性

玻璃钝化芯片，高可靠性和一致性
 低通态电流和高浪涌电流能力
 环保 RoHS 产品

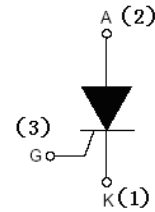
FEATURES

Glass-passivated mesa chip for reliability and uniform
 Low on-state voltage and High I_{TSM}
 RoHS products

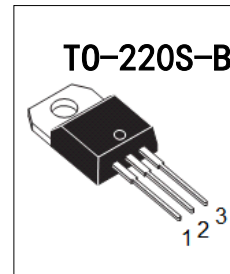
订货信息 ORDER MESSAGE

订货型号 Order codes		印记 Marking	封装 Package
有卤-条管	无卤-条管		
Halogen-Tube	halogen-Free-Tube		
CD2535H1-CD-B	CD2535H1-CD-BR	CD2535H1	TO-220S-B
CD2535H1-CB-B	CD2535H1-CB-BR	CD2535H1	TO-220S

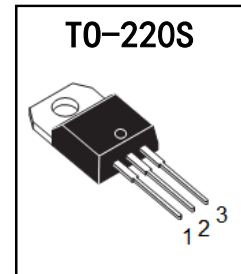
封装 Package



序号 Pin	引线名称 Description
1	阴极 K
2	阳极 A
3	门极 G



Non-insulated



Insulated



绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
断态重复峰值电压 Repetitive peak off-state voltage	V _{DRM}	1000	V
反向重复峰值电压 Repetitive peak reverse voltage	V _{RRM}	1000	V
通态平均电流 Average on-state current (half sine wave)	I _{T(AV)}	25	A
通态方均根电流 On-state RMS current (all conduction angles)	I _{T(RMS)}	40	A
非重复浪涌峰值通态电流 Non- repetitive surge peak on-state current (half sine wave ,t=10ms)	I _{TSM}	250	A
I ² t for fusing (t=10ms)	I ² t	312.5	A ² s
门极峰值电流 Peak gate current	I _{GM}	4	A
门极峰值电压 Peak gate voltage	V _{GM}	5	V
反向门极峰值电压 Peak reverses gate voltage	V _{RGM}	5	V
门极峰值功率 Peak gate power	P _{GM}	5	W
门极平均功率 Average gate power (over any 20ms period)	P _{G(AV)}	1	W
存储温度 Storage temperature	T _{stg}	-40~150	°C
操作结温 Operation junction temperature	T _J	125	°C

**静态特性 STATIC CHARACTERISTICS (T_c=25°C unless otherwise stated)**

项 目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 min	典型 typ	最大 max	单位 Unit
断态峰值重复电流 Peak Repetitive Blocking Current	I _{DRM}	V _{DM} = V _{DRM(MAX)} , T _j =125°C	-	-	4.0	mA
反向峰值重复电流 Peak Repetitive Reverse Current	I _{RPM}	V _{RM} = V _{RPM(MAX)} , T _j =125°C	-	-	4.0	mA
峰值通态电压 Peak on-state voltage	V _{TM}	I _{TM} =75A	-	-	1.60	V
门极触发电流 Gate trigger current	I _{GT}	V _{DM} =12V, I _T =0.1A	10	-	35	mA
门极触发电压 Gate trigger voltage	V _{GT}	V _{DM} =12V, I _T =0.1A	-	0.95	1.5	V
维持电流 Holding current	I _H	V _{DM} =12V, I _{GT} =0.5A	-	-	90	mA
擎住电流 Latching current	I _L	V _{DM} =12V, I _{GT} =0.1A	-	-	150	mA

动态特性 DYNAMIC CHARACTERISTICS (T_c=25°C unless otherwise stated)

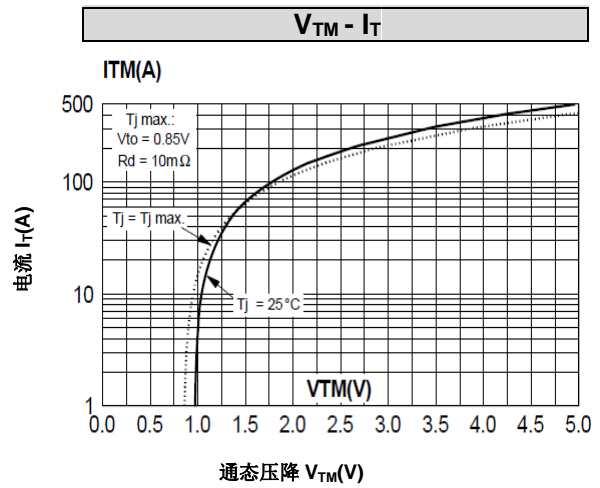
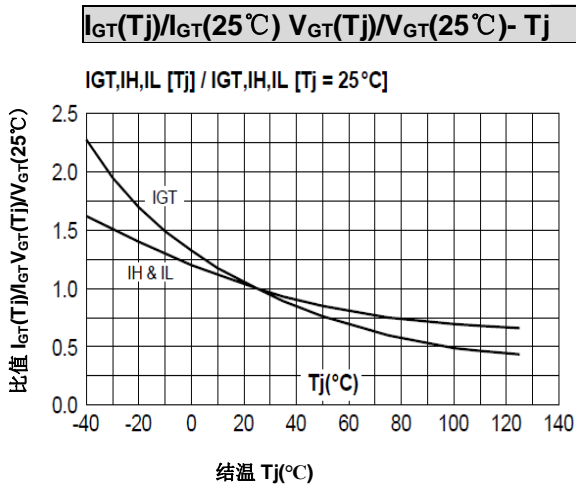
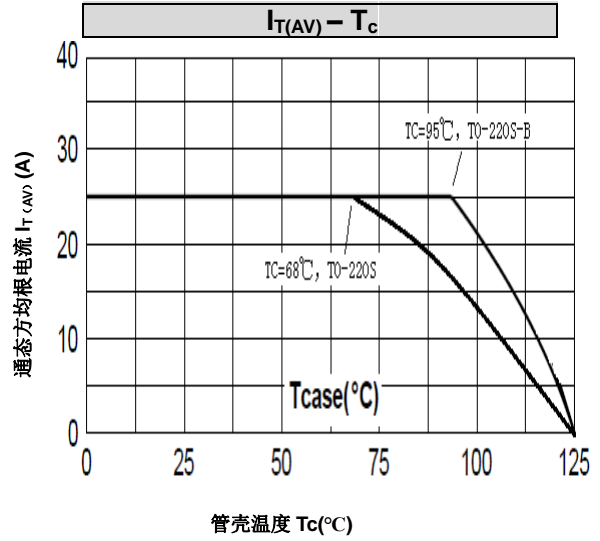
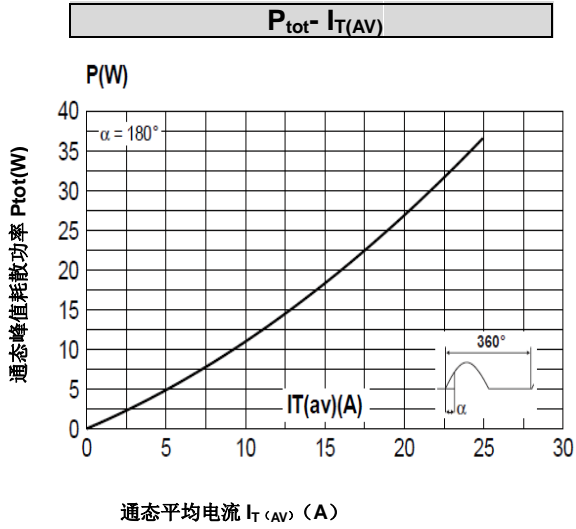
项 目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 min	典型 typ	最大 max	单位 Unit
断态临界电压上升率 Critical rate of rise of off- state voltage	dV/dt	V _{DM} =67% V _{DRM(MAX)} , T _j =125°C	1000	-	-	V/μs

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	值 value	单位 Unit
结到管壳的热阻 Thermal resistance junction to case	TO-220S-B R _{th(j-c)}	0.78 max	°C/W
结到管壳的热阻 Thermal resistance junction to case	TO-220S R _{th(j-c)}	1.5	°C/W



特征曲线 ELECTRICAL CHARACTERISTICS (curves)

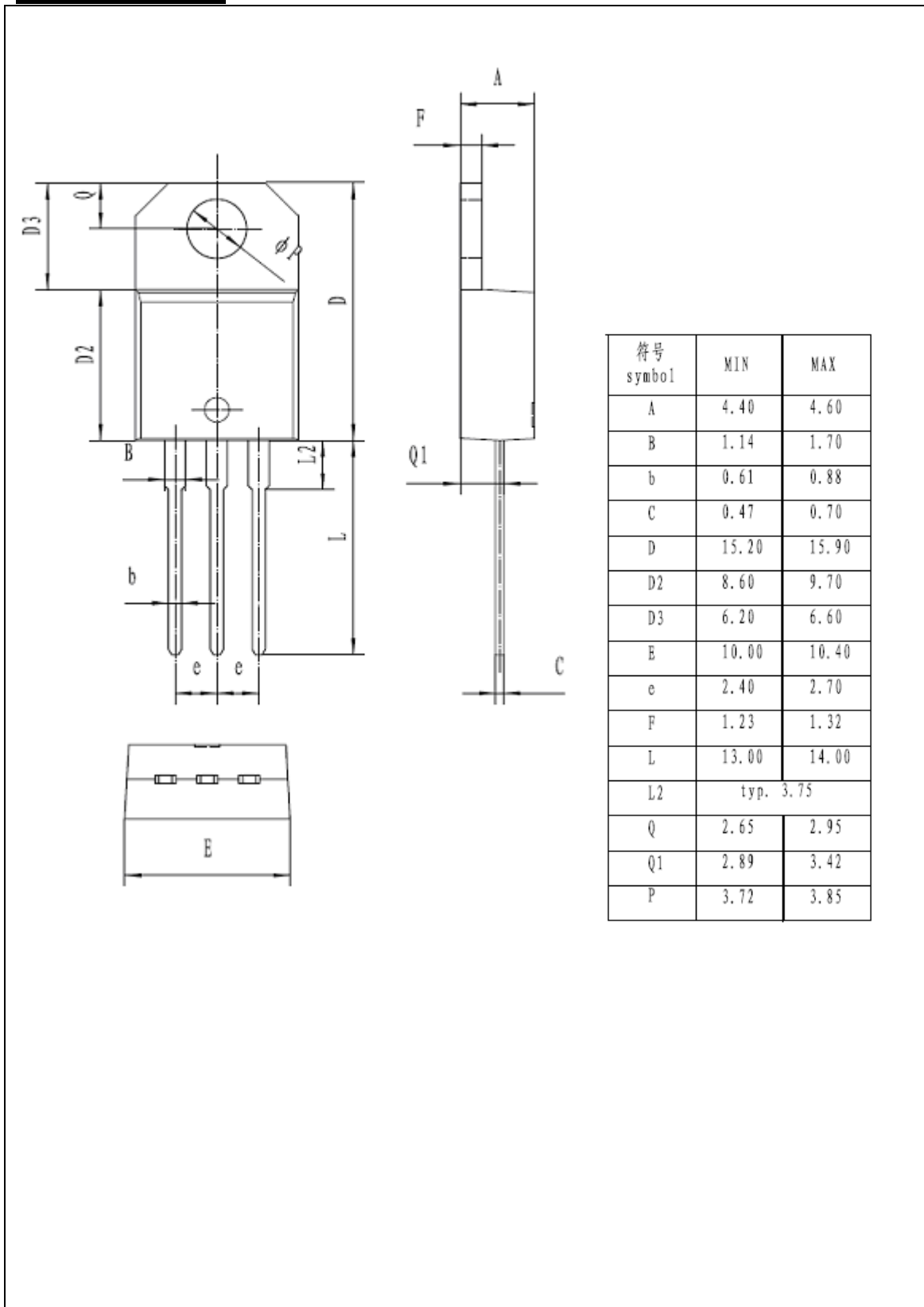




外形尺寸 PACKAGE MECHANICAL DATA

TO-220S-B/TO-220S

单位 Unit : mm





注意事项

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3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知。

NOTE

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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
4. Jilin Sino-microelectronics co., Ltd reserves the right to make changes in this. specification sheet and is subject to change without prior notice.

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